

Features

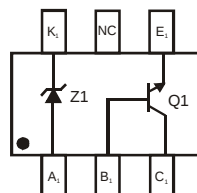
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Lead Free/RoHS Compliant Version (Notes 2 & 3)**
- **“Green” Device (Note 3)**

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, “Green” Molding Compound (Note 3) UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

Maximum Ratings, NPN Transistor Element (Q1) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	600	mA

Maximum Ratings, Zener Element (Z1) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ I _F = 10mA	V _F	0.9	V

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Product manufactured with date code WN (Week 45, 2009) and newer are built with Green Molding Compound and Lead-free plating. Product manufactured prior to date code WO are built with Tin-Lead plating, Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

Electrical Characteristics, NPN Transistor Element (Q1) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
Base Cutoff Current	I _{BL}	—	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	20 40 80 100 40	— — — 300 —	—	I _C = 100μA, V _{CE} = 1.0V I _C = 1.0mA, V _{CE} = 1.0V I _C = 10mA, V _{CE} = 1.0V I _C = 150mA, V _{CE} = 1.0V I _C = 500mA, V _{CE} = 2.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.40 0.75	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.75 —	0.95 1.2	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}	—	6.5	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}	—	30	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.0	15	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	40	500	—	
Output Admittance	h _{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f _T	250	—	MHz	V _{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	15	ns	V _{CC} = 30V, I _C = 150mA, V _{BE(off)} = 2.0V, I _{B1} = 15mA
Rise Time	t _r	—	20	ns	
Storage Time	t _s	—	225	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = I _{B2} = 15mA
Fall Time	t _f	—	30	ns	

Electrical Characteristics, Zener Element (Z1) @T_A = 25°C unless otherwise specified

Zener Voltage Range (Note 4)				Maximum Zener Impedance		Maximum Reverse Leakage Current (Note 4)	
V _Z @ I _{ZT}			I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK} = 0.5mA	I _R	@ V _R
Nom (V)	Min (V)	Max (V)	mA		Ω	μA	V
5.6	5.49	5.73	5	60	200	1.0	2.5

Notes: 4. Short duration pulse test used to minimize self-heating effect.

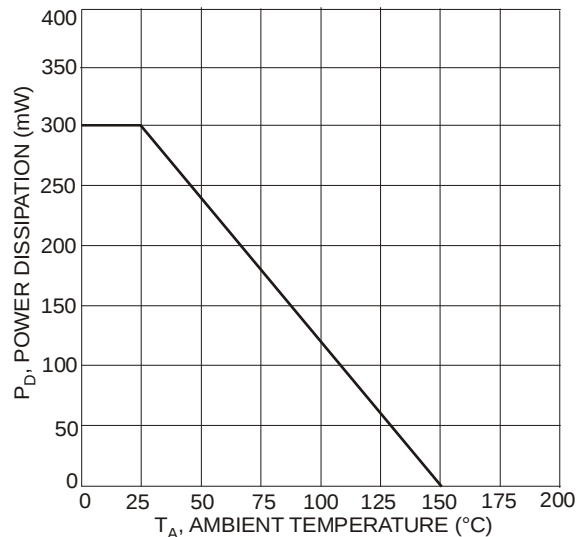
NPN Transistor Section (Q1)


Fig. 1 Power Dissipation vs. Ambient Temperature (Total Device)

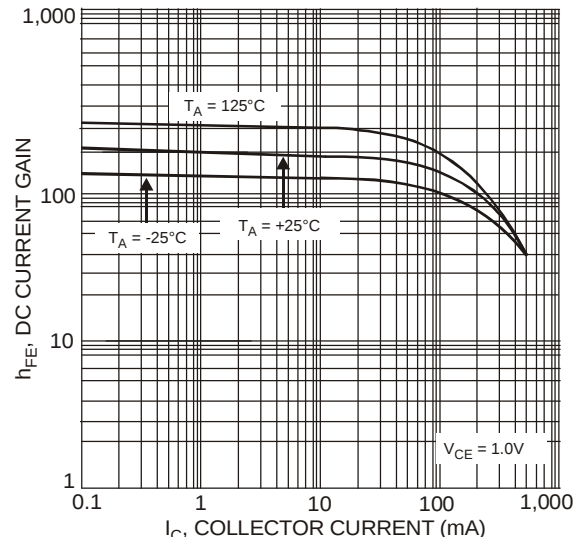


Fig. 2 Typical DC Current Gain vs. Collector Current

NPN Transistor Section (Q1)

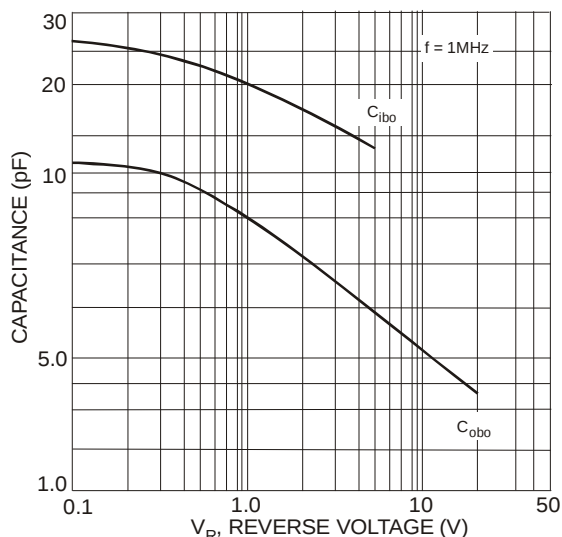


Fig. 3 Typical Capacitance Characteristics

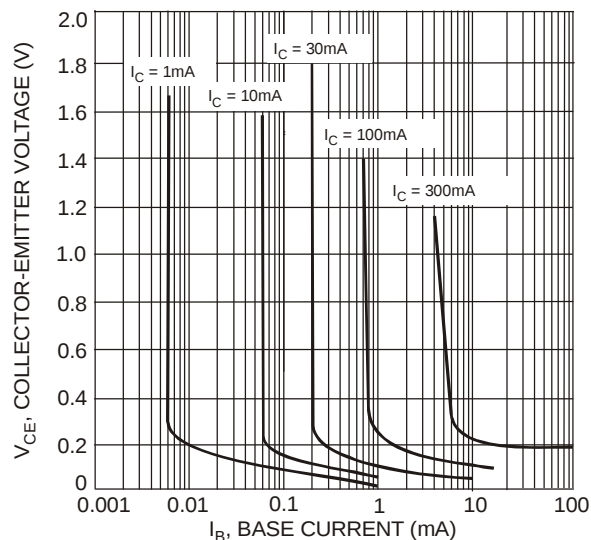


Fig. 4 Typical Collector Saturation Region

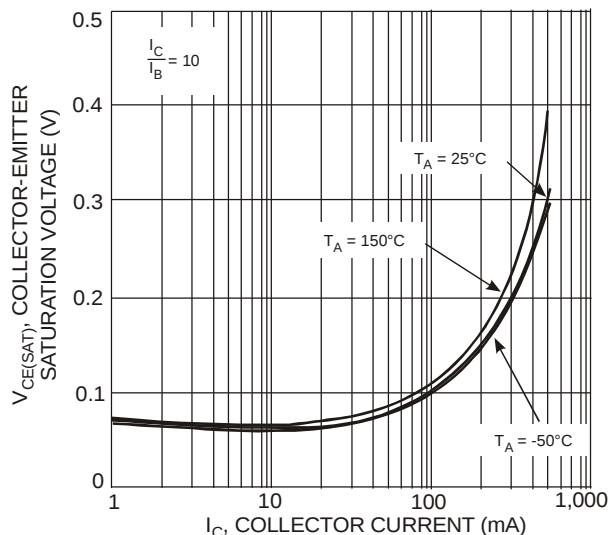


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

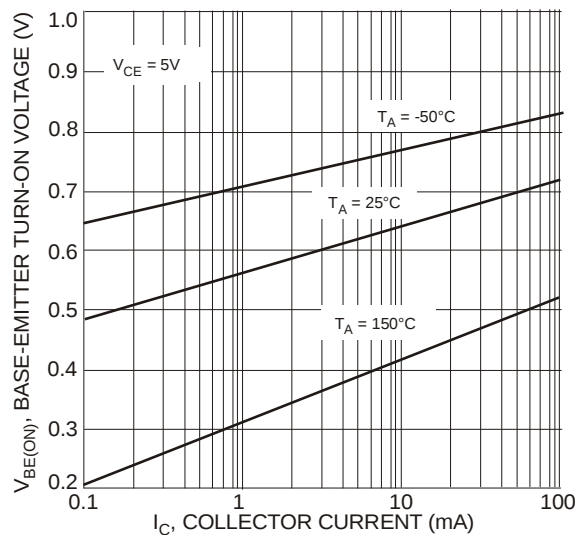


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

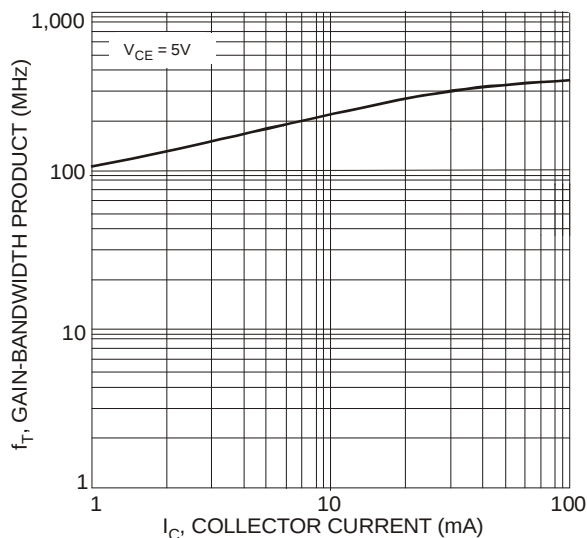
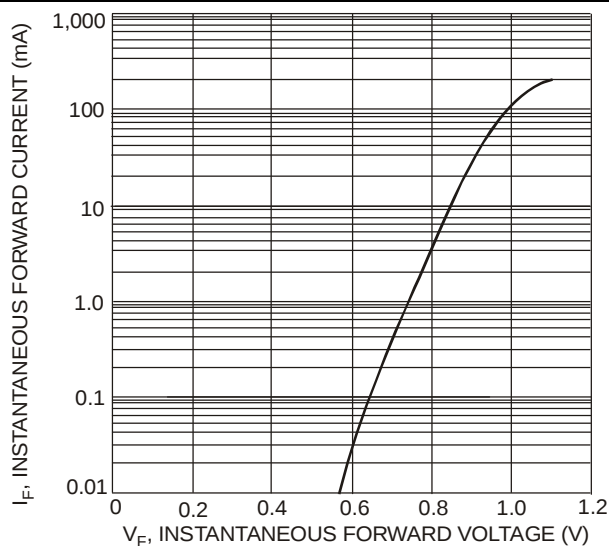


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current

Zener Section (Z1)

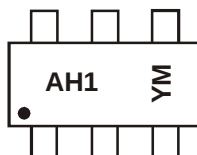


Ordering Information (Note 5)

Part Number	Case	Packaging
DVRN6056-7-F	SOT-26	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



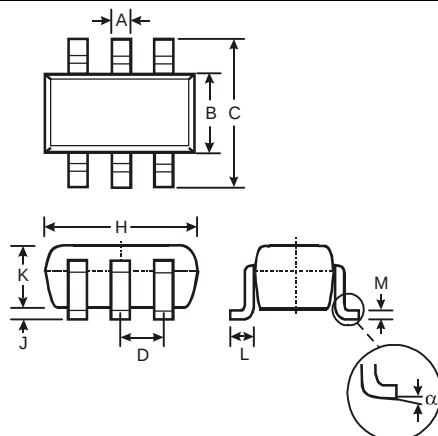
AH1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: P = 2003)
 M = Month (ex: 9 = September)

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	P	R	S	T	U	V	W	X	Y	Z	A	B	C

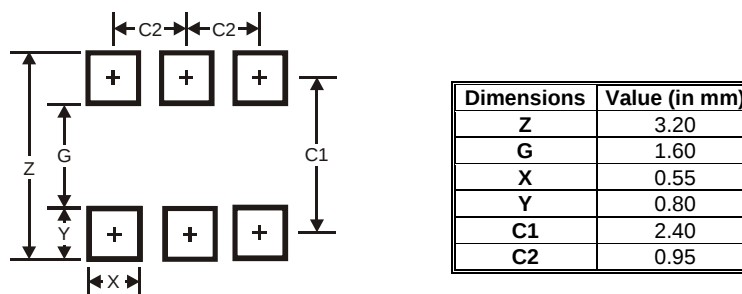
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



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